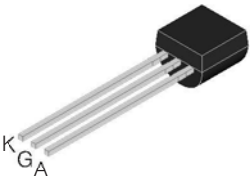
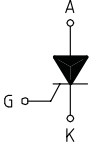


SENSITIVE GATE SCR

<p style="text-align: center;">TO92 (Plastic)</p>  <p style="text-align: center;">K G A</p> <p style="text-align: center;">FS01...A</p> 	<table style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 50%; vertical-align: top;"> <p>On-State Current 0.8 Amp</p> </td> <td style="width: 50%; vertical-align: top;"> <p>Gate Trigger Current < 200 μA</p> </td> </tr> <tr> <td colspan="2" style="text-align: center; vertical-align: top;"> <p>Off-State Voltage 200 V \div 800 V</p> </td> </tr> </table> <p>This series of Silicon Controlled Rectifiers uses a high performance PNPN technology.</p> <p>This part is intended for general purpose applications where high gate sensitivity is required.</p>	<p>On-State Current 0.8 Amp</p>	<p>Gate Trigger Current < 200 μA</p>	<p>Off-State Voltage 200 V \div 800 V</p>	
<p>On-State Current 0.8 Amp</p>	<p>Gate Trigger Current < 200 μA</p>				
<p>Off-State Voltage 200 V \div 800 V</p>					

Absolute Maximum Ratings, according to IEC publication No. 134

SYMBOL	PARAMETER	CONDITIONS	Value	Unit
$I_{T(RMS)}$	On-state Current	180° Conduction Angle, $T_c = 115\text{ }^\circ\text{C}$	0.8	A
$I_{T(AV)}$	Average On-state Current	Half Cycle, $\Theta = 180^\circ$, $T_c = 115\text{ }^\circ\text{C}$	0.5	A
I_{TSM}	Non-repetitive On-State Current	Half Cycle, 60 Hz	8	A
I_{TSM}	Non-repetitive On-State Current	Half Cycle, 50 Hz	7	A
I^2t	Fusing Current	$t_p = 10\text{ms}$, Half Cycle	0.24	A^2s
I_{GM}	Peak Gate Current	20 μ s max.	1	A
P_{GM}	Peak Gate Dissipation	20 μ s max.	2	W
$P_{G(AV)}$	Gate Dissipation	20 μ s max.	0.1	W
T_j	Operating Temperature		(-40 to + 125)	$^\circ\text{C}$
T_{stg}	Storage Temperature		(-40 to + 150)	$^\circ\text{C}$
T_{sld}	Soldering Temperature	10s max.	260	$^\circ\text{C}$

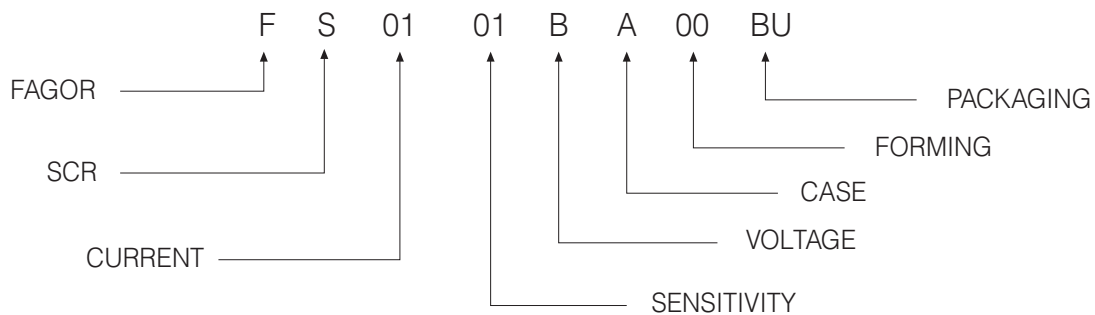
SYMBOL	PARAMETER	CONDITIONS	VOLTAGE					Unit
			B	D	M	S	N	
V_{DRM} V_{RRM}	Repetitive Peak Off State Voltage	$R_{GK} = 1\text{ k}\Omega$	200	400	600	700	800	V

SENSITIVE GATE SCR

Electrical Characteristics

SYMBOL	PARAMETER	CONDITIONS	SENSITIVITY						Unit	
			01	02	03	04	18	11		
I _{GT}	Gate Trigger Current	V _D = 12 V _{DC} , R _L = 140Ω, T _j = 25 °C	MIN	1		20	15	0.5	4	μA
			MAX	20	200	200	50	5	25	
V _{GT}	Gate Trigger Voltage	V _D = 12 V _{DC} , R _L = 140Ω, T _j = 25 °C	MAX	0.8						V
V _{GD}	Gate Non Trigger Voltage	V _D = V _{DRM} , R _L = 3.3kΩ, R _{GK} = 220Ω T _j = 125 °C	MIN	0.1						V
V _{RGM}	Reverse Gate Voltage	I _{RG} = 10μA,	MIN	8						V
I _H	Holding Current	I _T = 50 mA, R _{GK} = 1kΩ, T _j = 25 °C	MAX	5						mA
I _L	Latching Current	I _G = 1 mA, R _{GK} = 1 kΩ	MAX	6						mA
dV / dt	Critical Rate of Voltage Rise	V _D = 0.67 x V _{DRM} , R _{GK} = 1 kΩ, T _j = 125 °C	MIN	80	75	20	15	80	75	V/μs
dI / dt	Critical Rate of Current Rise	I _G = 2 x I _{GT} , tr ≤ 100 ns, f = 60 Hz, T _j = 125 °C	MIN	50						A/μs
V _{TM}	On-state Voltage	at I _T = 1.6 Amp, tp = 380 μs, T _j = 25 °C	MAX	1.95						V
V _{t0}	Threshold Voltage	T _j = 125 °C	MAX	0.95						V
r _d	Dynamic resistance	T _j = 125 °C	MAX	600						mΩ
I _{DRM} / I _{RRM}	Off-State Leakage Current	V _D = V _{DRM} , R _{GK} = 1kΩ, T _j = 125 °C	MAX	100						μA
		V _R = V _{RRM} , T _j = 25 °C	MAX	1						μA
R _{th(j-c)}	Thermal Resistance Junction-Amb for DC	for AC 360° conduction angle		80						°C/W
R _{th(j-a)}	Thermal Resistance Junction-Amb for DC	S = 1cm ²		150						°C/W

PART NUMBER INFORMATION



SENSITIVE GATE SCR

Fig. 1: Maximum average power dissipation versus average on-state current

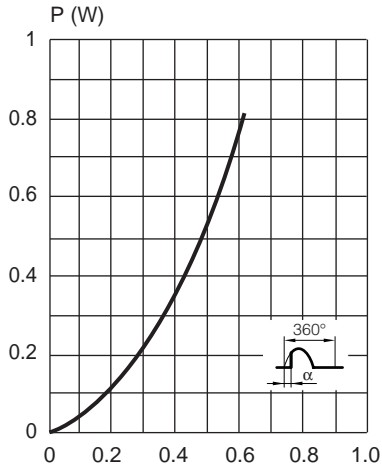


Fig. 3: Relative variation of thermal impedance junction to case versus pulse duration

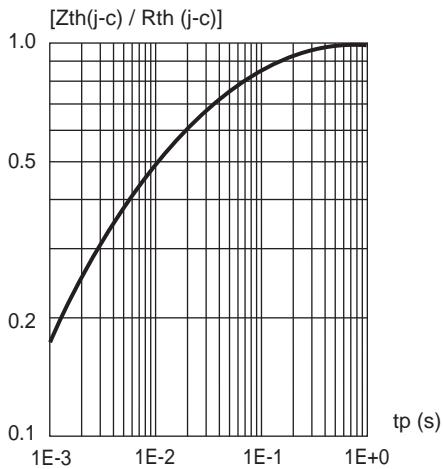


Fig. 5: Relative variation of holding current versus gate-cathode resistance (typical values).

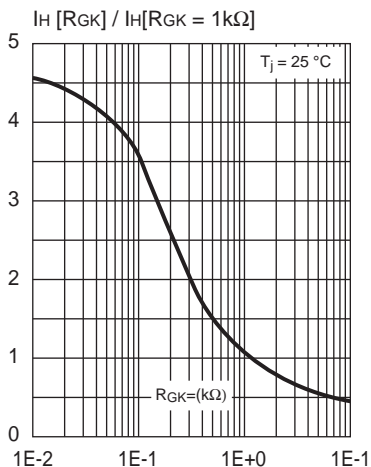


Fig. 2: Average and D.C. on-state current versus case temperature

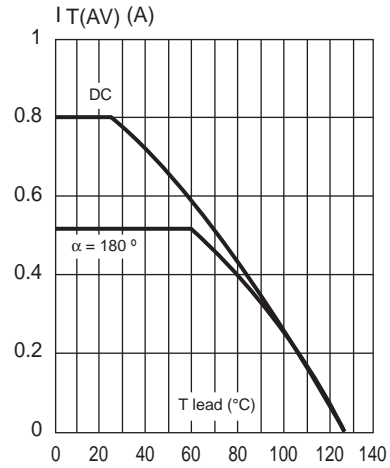


Fig. 4: Relative variation of gate trigger current, holding and latching current versus junction temperature

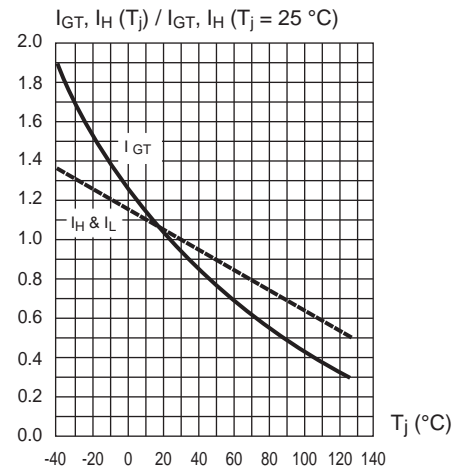
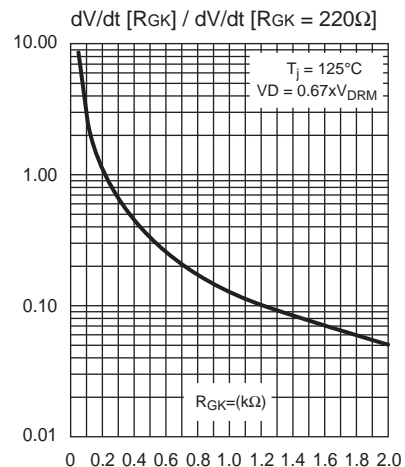


Fig. 6: Relative variation of dV/dt immunity versus gate-cathode resistance (typical values).



SENSITIVE GATE SCR

Fig. 7: Relative variation of dV/dt immunity versus gate-cathode resistance (typical values).

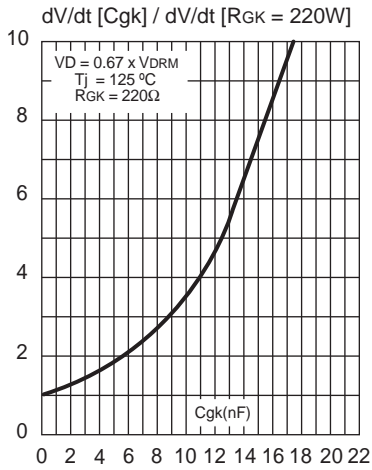


Fig. 8: Non repetitive surge peak on-state current versus number of cycles.

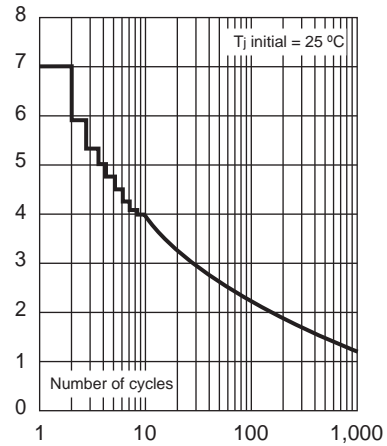


Fig. 9: Non repetitive surge peak on-state current for a sinusoidal pulse with width: $t_p < 10$ ms, and corresponding value of I^2t .

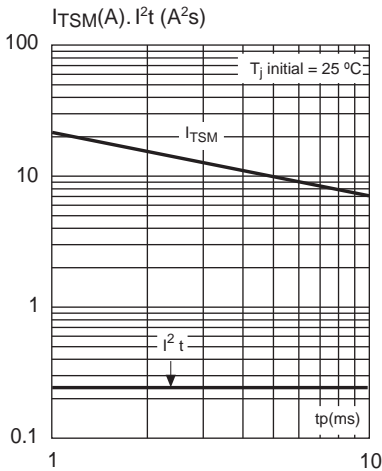
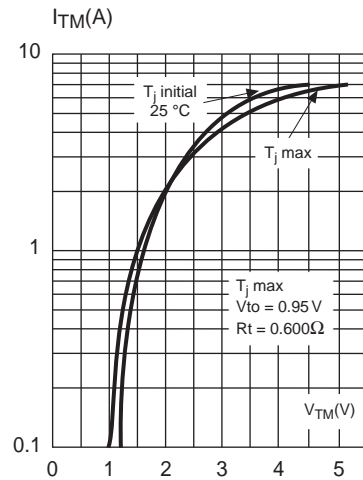


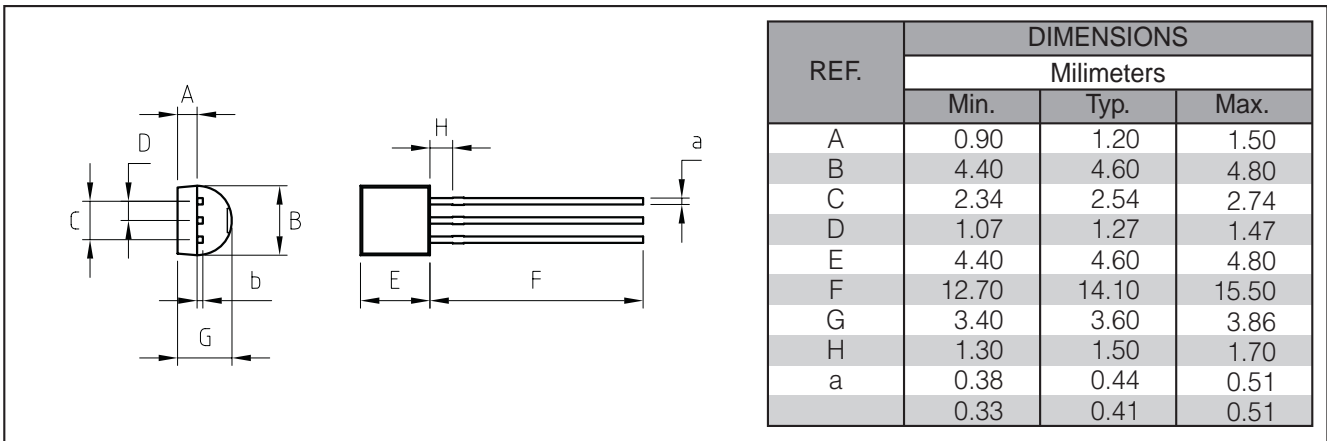
Fig. 10: On-state characteristics (maximum values)



SENSITIVE GATE SCR

PACKAGE MECHANICAL DATA

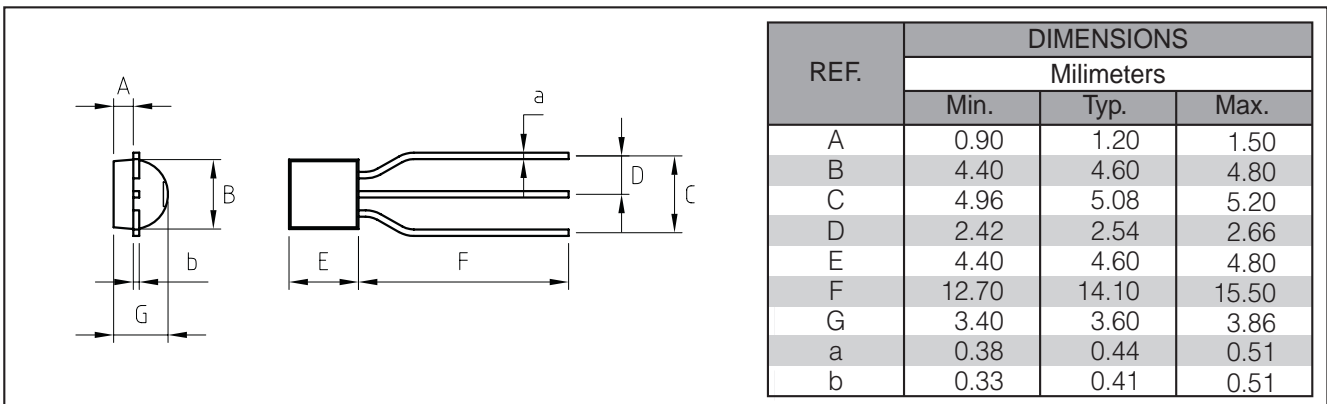
TO92



Marking: type number
Weight: 0.2 g

PACKAGE MECHANICAL DATA

TO92 (FOR TAPE & REEL)



Marking: type number
Weight: 0.2 g